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N-Channel 60 V (D-S) MOSFET

Pho
RoHS
COMPLIANT

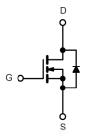
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a (Max.)		
60	29 at V _{GS} = 10 V	35		
	36 at V _{GS} = 4.5 V	30		

FEATURES

- DT-Trench Power MOSFET
- 100% Rg and UIS Tested

APPLICATIONS

- Motor Drive
- Power Tools



N-Channel MOSFET

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ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I-	35		
	T _C = 100 °C	- I _D	25 ^a		
Pulsed Drain Current		I _{DM}	90	Α	
Continuous Source Current (Diode Conduction)		I _S	35		
Avalanche Current		I _{AS}	30		
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	29 ^c	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	45	· w	
iviaximum Fower Dissipation	T _A = 25 °C] 'D [2.3 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	- R _{thJA}	13	18	°C/W
	Steady State		35	50	
Maximum Junction-to-Case		R _{thJC}	2.0	3.0	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$

Rev. N



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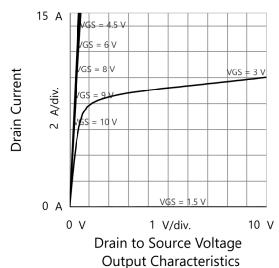
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static				<u> </u>		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 60 V, V _{GS} = 0 V			1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	35			Α
	R-o.	V _{GS} = 10 V, I _D = 15 A		29	36	mΩ
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		36	46	11122
Forward Transconductance ^b	9 _{fs}	V _{DS} = 5 V, I _D = 20 A		40		S
Dynamic						
Input Capacitance	C _{iss}			826		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		51		
Reverse Transfer Capacitance	C _{rss}			43		
Total Gate Charge ^c	Qg			20	30	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		1.9		nC
Gate-Drain Charge ^c	Q_{gd}			4.5		
Turn-On Delay Time ^c	t _{d(on)}			13		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, R}_{L} = 1.0 \Omega$ $I_{D} = 15 \text{ A, V}_{GEN} = 10 \text{ V, R}_{g} = 2.5 \Omega$		46		
Turn-Off Delay Time ^c	t _{d(off)}			25		ns
Fall Time ^c	t _f			10		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)	<u> </u>	•		
Pulsed Current	I _{SM}				90	Α
Diode Forward Voltage	V _{SD}	I _F = 1 A, V _{GS} = 0 V		0.6	1.0	V
Reverse Recovery Time	t _{rr}	I _F = 15 A, di/dt = 500 A/μs		25	50	ns
Reverse Recovery Charge	Q _{rr}	I _F = 15 A, di/dt = 500 A/μs		45	100	nC

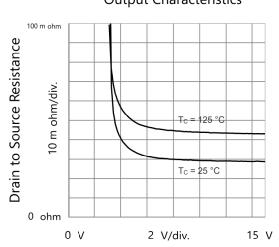
- a. For design aid only; not subject to production testing. b. Pulse test; pulse width 300 μs , duty cycle 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

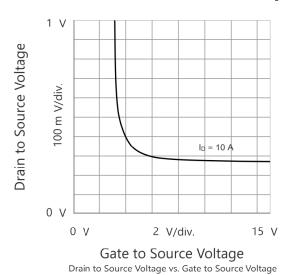


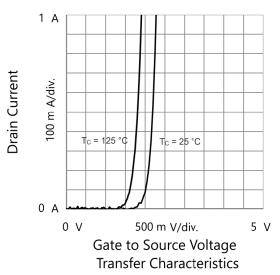
TYPICAL CHARACTERISTICS (25 °C unless noted)

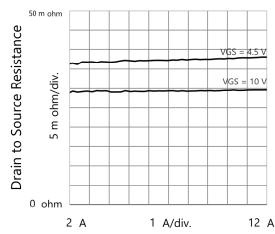




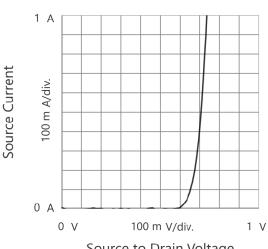
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage







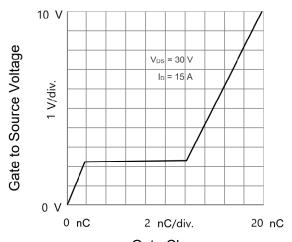
Drain Current
Drain to Source Resistance vs. Drain Current



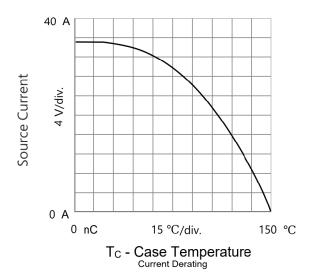
Source to Drain Voltage Body Diode Forward Characteristics

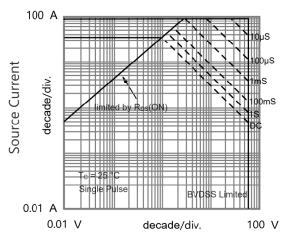


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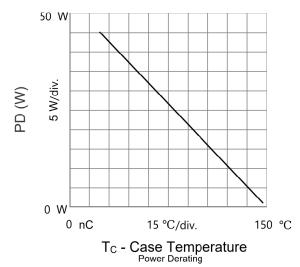


Gate Charge
Gate to Source Voltage vs. GateCharge





Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



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